

HD1520FX

HIGH VOLTAGE NPN POWER TRANSISTOR FOR HIGH DEFINITION CRT DISPLAYS

- STATE-OF-THE-ART TECHNOLOGY: DIFFUSED COLLECTOR "ENHANCED GENERATION" EHVS1
- WIDER RANGE OF OPTIMUM DRIVE CONDITIONS
- LESS SENSITIVE TO OPERATING TEMPERATURE VARIATION
- n FULLY INSULATED POWER PACKAGE U.L. COMPLIANT

APPLICATIONS

HORIZONTAL DEFLECTION FOR LARGE AND FLAT SCREEN 100 Hz COLOR TVs

DESCRIPTION

The device is manufactured using Diffused Collector in Planar technology adopting "Enhance High Voltage Structure" (EHVS1) developed to fit High-Definition CRT displays.

The new HD product series show improved silicon efficiency bringing updated performance to the Horizontal Deflection stage.

Figure 1: Package

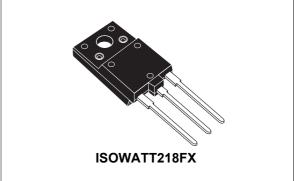


Figure 2: Internal Schematic Diagram

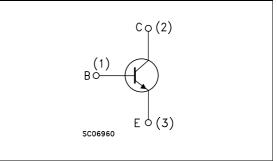


Table 1:

Part Number Marking		Package	Packaging	
HD1520FX	HD1520FX	ISOWATT218FX	TUBE	

Table 2: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit	
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)	1500	V	
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	700	V	
V_{EBO}	Emitter-Base Voltage (I _C = 0)	10	V	
Ι _C	Collector Current	15	A	
I _{CM}	Collector Peak Current (t _p < 5ms)	22	Α	
Ι _Β	Base Current	8	Α	
I _{BM}	Base Peak Current (t _p < 5ms)	12	Α	
P _{tot}	Total Dissipation at $T_{\rm C}$ = 25 °C	64	W	
V _{ins}	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V	
		Rev. 1		

May 2005

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Symbol	Parameter	Value	Unit
T _{stg}	Storage Temperature	-65 to 150	°C
TJ	Max. Operating Junction Temperature	150	°C

Table 3: Thermal Data

R _{thj-case}	Thermal Resistance Junction-Case	Max	1.95	°C/W
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Table 4: Electrical Characteristics (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test C	onditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current	V _{CE} = 1500 V				0.2	mA
	(V _{BE} = 0)	V _{CE} = 1500 V	T _C = 125 °C			2	mA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5 V				10	μA
	$(I_{\rm C} = 0)$						
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	I _C = 100 mA		700			V
	(I _B = 0)						
V _{EBO}	Emitter-Base Voltage	I _E = 10 mA		10			V
	$(I_{\rm C} = 0)$						
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 9 A	I _B = 1.8 A			3	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 9 A	I _B = 1.8 A			1.3	V
h _{FE}	DC Current Gain	I _C = 1 A	V _{CE} = 5 V		26		
		I _C = 9 A	V _{CE} = 1 V		5		
		I _C = 9 A	V _{CE} = 5 V	5.5		9.5	
	INDUCTIVE LOAD	I _C = 9 A	f _h = 31250 Hz				
t _s	Storage Time	I _{B(on)} = 1.3 A	I _{B(off)} = -4.2 A		3.2	4	μs
t _f	Fall Time	L _{BB(on)} = 1.9 μH	$V_{BE(off)} = -2.7 V$		220	300	ns
		V _{CE(fly)} = 1040 V					

* Pulsed: Pulsed duration = 300 μ s, duty cycle \leq 1.5 %.



Figure 3: Safe Operating Area

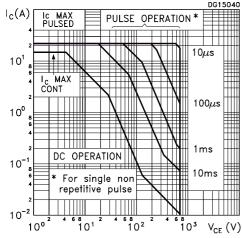
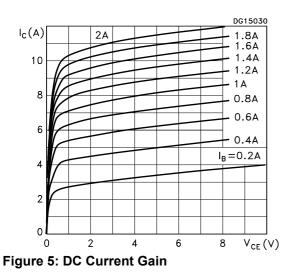


Figure 4: Output Chatacterisctics



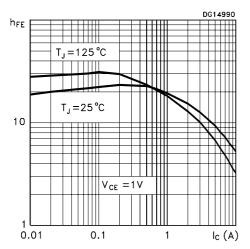


Figure 6: Derating Curve

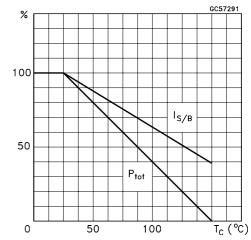


Figure 7: Reverse Biased SOA

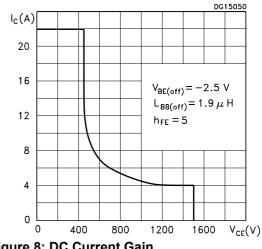
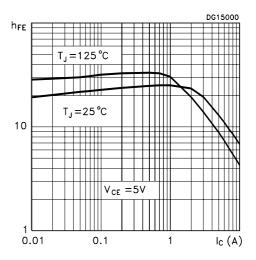


Figure 8: DC Current Gain



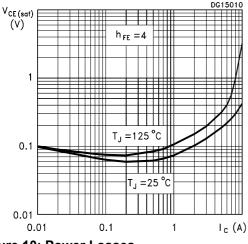


Figure 9: Collector-Emitter Saturation Voltage



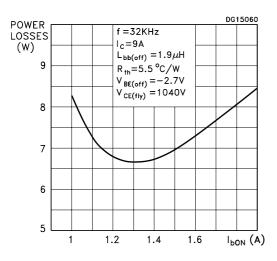


Figure 11: Base-Emitter Saturation Voltage

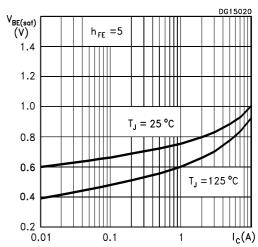
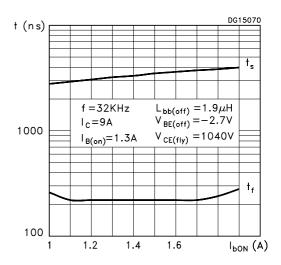


Figure 12: Inductive Load Switching Time





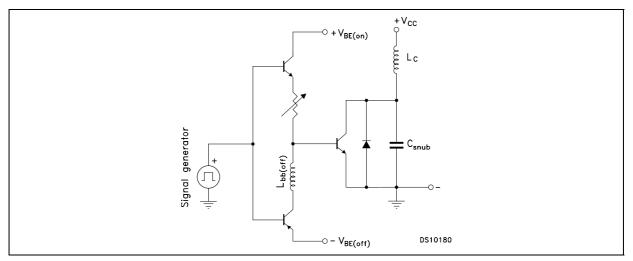
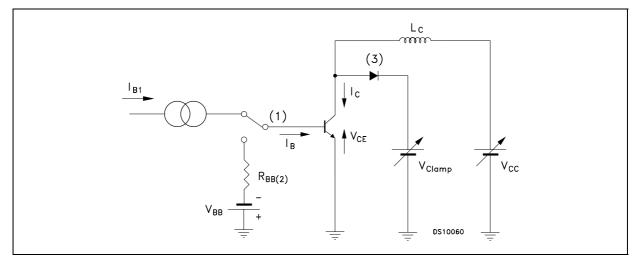
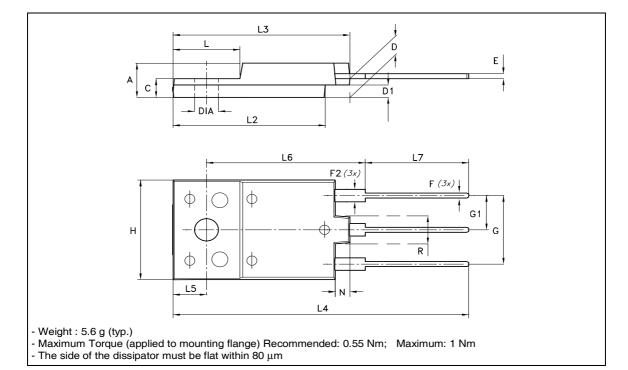


Figure 14: Reverse Biased Safe Operating Area Test Circuit





DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	5.30		5.70	0.209		0.224
С	2.80		3.20	0.110		0.126
D	3.10		3.50	0.122		0.138
D1	1.80		2.20	0.071		0.087
Е	0.80		1.10	0.031		0.043
F	0.65		0.95	0.026		0.037
F2	1.80		2.20	0.071		0.087
G	10.30		11.50	0.406		0.453
G1		5.45			0.215	
Н	15.30		15.70	0.602		0.618
L	9.0		10.20	0.354		0.402
L2	22.80		23.20	0.898		0.913
L3	26.30		26.70	1.035		1.051
L4	43.20		44.40	1.701		1.748
L5	4.30		4.70	0.169		0.185
L6	24.30		24.70	0.957		0.972
L7	14.60		15.00	0.575		0.591
N	1.80		2.20	0.071		0.087



ISOWATT218FX MECHANICAL DATA

Figure 5: Revision History

Version	Release Date	Change Designator
27-May-2005	0.1	Initial Release.



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